## What is FeRAM?

September 2024





## **Introduction Flow**









## **1. Overview of FeRAM**





#### FeRAM Lineup

- Three interface: I2C, SPI, and Parallel
- Memory density: 4Kbit to 8Mbit

Temperature range: Operating at maximum 125°C

Interface	I2C	SPI	Parallel
Density	4K to 1Mbit	16K to 8Mbit	256K to 8Mbit
Supply Voltage	1.7 to 1.95V / 1.8 to 3.6V 2.7 to 3.6V / 2.7 to 5.5V	1.65 to 1.95V / 1.7 to1.95V 1.7 to 3.6V / 1.8 to 3.6V 2.7 to 3.6V / 2.7 to 5.5V	1.8 to 3.6V 2.7 to 3.3V
Operating Temperature	-40°C to +125°C -40°C to +105°C -40°C to +95°C -40°C to +85°C	-40°C to +125°C -40°C to +105°C -40°C to +95°C -40°C to +85°C	+40°C to +105°C -40°C to +85°C
Package	SOP, SON, DFN	SOP, SON, DFN, WL-CSP	SOP, TSOP, FBGA

\*: Please confirm detailed specs by each product.

[As of September 2024]



## 2. Applications using FeRAM



#### Where is FeRAM used?

Used in all kind of market segments, especially strong in the public services

Suitable for frequent data logging requirement





## 3. History of shipment



#### Quantity of FeRAM shipped

Production since 1999, total shipment is more than **4 billion pcs** 

#### Countries FeRAM shipped

Used in over **60 countries**, more than **200 types** of applications





## 3. History of receiving awards



#### History of receiving awards for FeRAM

Our company received **11 awards in 15 years** from domestic academic societies and government agencies

Year	Award Name	Organizer
2001	第8回LSIデザイン・オブ・ザ・イヤー優秀賞	半導体産業新聞社
2004	CORPORATE INOVATION AWARD	ISIF
2004	文部科学大臣表彰 研究功績者(研究功績者)	文部科学省
2007	第2回 ものづくり日本大賞 優秀賞	経済産業省等
2011	産学官連携功労者表彰 日本経済団体連合会会長賞	内閣府等
2013	応用物理学会フェロー表彰	応用物理学会
2013	文部科学大臣奨励賞、電気科学技術奨励賞	電気科学技術奨励会
2014	大河内記念技術賞	大河内記念会
2014	文部科学大臣表彰 科学技術賞(開発部門)	文部科学省
2014	第14回 山﨑貞一賞	材料科学技術振興財団
2015	紫綬褒章	内閣府





#### Features of FeRAM

Having advantages of both non-volatile and volatile memories



Overview Usage History Features Solutions

#### Comparison to other memory devices

Having advantages of both non-volatile and volatile memories

ltem	FeRAM	EEPROM	Flash memory	SRAM
Memory Type	Non-volatile	Non-volatile	Non-volatile	Volatile
Data Backup Battery	Νο	No	No	Yes
Guaranteed Write Cycles	100 trillion	1 million	100 thousand	Unlimited
Write Method	Overwrite	Erase + Write	Erase + Write	Overwrite
Write Cycle Time	120ns	5ms	10µs	55ns
Booster Circuit	Νο	Yes	Yes	No





#### FeRAM Feature – High Read/Write Endurance

Merit: Guarantees 100 trillion times of read/write cycles

Reason: Enables by FeRAM cell structure with ferroelectric property



![](_page_10_Picture_6.jpeg)

![](_page_11_Figure_1.jpeg)

#### FeRAM Feature – Fast Write Speed

Merit: Write cycle time of 120ns, faster than EEPROM

• Reason: Data erase operation is not needed during write operation

![](_page_11_Figure_5.jpeg)

![](_page_12_Figure_1.jpeg)

#### FeRAM Feature – Low Power Consumption

Merit #1: Lower power in data writing, due to shorter write time

Merit #2: No backup battery, due to data retention current is not necessary

![](_page_12_Figure_5.jpeg)

5MHz, 1s

## **5. Solutions by FeRAM to Customer Issues**

![](_page_13_Figure_1.jpeg)

#### Customer Issues and Solutions

If you have the following concerns, consider solution by FeRAM

![](_page_13_Figure_4.jpeg)

## 5. Solutions by FeRAM to Customer Issues

![](_page_14_Figure_1.jpeg)

![](_page_14_Figure_2.jpeg)

#### Supports to evaluate our FeRAM device

- Simulation models (Verilog, IBIS) for software evaluation
- Providing FeRAM via online to buy a few samples

![](_page_14_Picture_6.jpeg)

# RAMXEED Our Memory, Your Future.

![](_page_15_Picture_1.jpeg)